L Number	Hits	Search Text	DB	Time stamp
1	86	(tec or thermal near2 expansion near2	USPAT; US-PGPUB;	2004/09/28 11:13
		coefficient).AB. and 117/\$4.ccls.	EPO; JPO; DERWENT;	11.13
2	2088	(tec or thermal near2 expansion near2	<pre>IBM_TDB USPAT;</pre>	2004/09/28
2	2000	coefficient) near15 (warp\$5 or bow\$4)	US-PGPUB; EPO; JPO;	11:14
		·	DERWENT; IBM TDB	
3	45	(tec or thermal near2 expansion near2 coefficient) near15 (warp\$5 or bow\$4)	USPĀT; US-PGPUB;	2004/09/28 11:36
		same epitax\$5	EPO; JPO; DERWENT;	
4	162	(tec or thermal near2 expansion near2	IBM_TDB USPAT;	2004/09/28
		coefficient) near15 (warp\$5 or bow\$4) and epitax\$5	US-PGPUB; EPO; JPO;	11:37
	: :		DERWENT; IBM_TDB	
5	26	(tec or thermal near2 expansion near2 coefficient) near15 (warp\$5 or bow\$4)	USPAT; US-PGPUB;	2004/09/28 11:56
	-	near10 (reduc\$5) and epitax\$5	EPO; JPO; DERWENT;	
<i>c</i>	. 1	/wass on gallium near? arsonide) near10	IBM_TDB USPAT;	2004/09/28
6	1	(gaas or gallium near2 arsenide) near10 epitax\$5 near10 temperature near10 "1000"	US-PGPUB;	11:57
			EPO; JPO; DERWENT;	
7	43	(gaas or gallium near2 arsenide) near10	IBM_TDB USPAT;	2004/09/28
		temperature near10 "1000"	US-PGPUB; EPO; JPO;	11:59
			DERWENT; IBM TDB	
8	410	(titanium or tungsten or tantalum or	USPAT; US-PGPUB;	2004/09/28
		molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10	EPO; JPO;	12.02
		temperature	DERWENT; IBM_TDB	
9	2	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2	USPAT; US-PGPUB;	2004/09/28 12:01
		silicide near10 deposit\$5 near10 temperature near5 "650"	EPO; JPO; DERWENT;	
1.0			IBM_TDB USPAT;	2004/09/28
10	9	molybdenum or cobalt or nickel) near2	US-PGPUB;	12:02
		silicide near10 deposit\$5 near10 temperature near5 "600"	EPO; JPO; DERWENT;	
11	1		IBM_TDB USPAT;	2004/09/28
	.)	molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10	US-PGPUB; EPO; JPO;	12:02
		temperature near5 "550"	DERWENT; IBM TDB	
12	214	((titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2	USPAT; US-PGPUB;	2004/09/28 14:32
-		silicide near10 deposit\$5 near10	EPO; JPO;	
		temperature) and @py<2001	DERWENT; IBM_TDB	0004/00/00
13	2228	(sin or silicon adj nitride) near10 deposit\$5 near10 temperature	USPAT; US-PGPUB;	2004/09/28 14:34
			EPO; JPO; DERWENT;	
14	982	((sin or silicon adj nitride) near10	IBM_TDB USPAT;	2004/09/28
14	902	deposit\$5 near10 temperature) and	US-PGPUB;	14:33
		@py<2000	EPO; JPO; DERWENT;	
	1		IBM TDB	

			TIOD NO.	2004/00/20
15	1639	<pre>(sin or silicon adj nitride) near10 deposit\$5 near5 temperature</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 14:34
			IBM TDB	
16	1296	(sin or silicon adj nitride) near5 deposit\$5 near5 temperature	USPĀT; US-PGPUB;	2004/09/28 14:34
			EPO; JPO; DERWENT; IBM TDB	
17	666	(sin or silicon adj nitride) near5	USPAT;	2004/09/28
		deposit\$5 near2 temperature	US-PGPUB; EPO; JPO;	14:36
			DERWENT; IBM TDB	
18	283	((sin or silicon adj nitride) near5	USPĀT;	2004/09/28
		deposit\$5 near2 temperature) and @py<2000	US-PGPUB; EPO; JPO;	14:35
		·	DERWENT;	
10	0	(sin or silicon adj nitride) near5	<pre>IBM_TDB USPAT;</pre>	2004/09/28
19		deposit\$5 near2 temperature near5 "1050"	US-PGPUB;	14:36
			EPO; JPO; DERWENT;	
		_	IBM_TDB	2224/22/22
20	2	(sin or silicon adj nitride) near5 deposit\$5 near2 temperature near5 "1000"	USPAT; US-PGPUB;	2004/09/28 14:36
		depositoro medili compolacida medili ili	EPO; JPO;	
			DERWENT; IBM TDB	
21	140	(sin or silicon adj nitride) near5	USPAT;	2004/09/28 14:40
		deposit\$5 near2 temperature near5 high	US-PGPUB; EPO; JPO;	14:40
			DERWENT; IBM TDB	
22	20	thermal near10 (sin or silicon near2	USPĀT;	2004/09/28
		nitride) same (jig or boat)	US-PGPUB; EPO; JPO;	14:43
			DERWENT;	
23	3	"0713245"	IBM_TDB USPAT;	2004/09/28
23		0710210	US-PGPUB;	14:43
			EPO; JPO; DERWENT;	
		H7122454	IBM_TDB USPAT;	2004/09/28
24	8	"713245"	US-PGPUB;	14:44
			EPO; JPO; DERWENT;	
			IBM_TDB	0004/00/00
25	98	(sin or silicon near2 nitride) near10 temperature near2 ("1100" or "1000" or	USPAT; US-PGPUB;	2004/09/28
		"1050" or "1200")	EPO; JPO;	
.			DERWENT; IBM_TDB	
26	47	1 = 2	USPĀT; US-PGPUB;	2004/09/28 14:56
		or "al.sub.2o.sub.3")	EPO; JPO;	13.00
			DERWENT; IBM TDB	
27	27		USPĀT;	2004/09/28
	*:	near2 oxide or "sio.sub.2") near10 deposit\$5 near2 temperature near5 ("850"	US-PGPUB; EPO; JPO;	15:26
	13 16	or "900" or "950" or "800")	DERWENT;	
28	142	mocvd near10 (gan or gallium adj nitride)	<pre>IBM_TDB USPAT;</pre>	2004/09/28
		near10 (temperature)	US-PGPUB;	15:28
			EPO; JPO; DERWENT;	
			IBM TDB	

29	12		USPAT;	2004/09/28
		near10 epitax\$6 near10 (temperature)	US-PGPUB; EPO; JPO;	15:29
			DERWENT;	
			IBM TDB	
30	0		USPĀT;	2004/09/28
		adj nitride) near10 (temperature) same	US-PGPUB;	15:29
		epitax4	EPO; JPO;	
			DERWENT; IBM TDB	
31	34	(mocvd or movpe) near10 (gan or gallium	USPAT;	2004/09/28
31		adj nitride) near10 (temperature) same	US-PGPUB;	17:09
		epitax\$4	EPO; JPO;	
			DERWENT;	
33	0	udea near2 tetsuzo.in. and (warp\$ or	IBM_TDB USPAT;	2004/09/28
32	"	bow\$4)	US-PGPUB;	17:10
		Dowy 17	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00
33	12	· -	USPAT;	2004/09/28 17:10
1		bow\$4)	US-PGPUB; EPO; JPO;	17.10
			DERWENT;	
			IBM_TDB	
-	353	olsen.in. and bow\$3	USPAT;	2004/02/09
			US-PGPUB;	18:08
			EPO; JPO; DERWENT;	
	:		IBM TDB	
_	2	olsen.in. and bow\$3 near10 wafer	USPAT;	2004/02/09
1			US-PGPUB;	18:09
			EPO; JPO;	
			DERWENT; IBM TDB	
_	1280	bow\$3 near10 wafer	USPAT;	2004/02/09
			US-PGPUB;	18:09
			EPO; JPO;	
			DERWENT; IBM TDB	
_	38	 bow\$3 near10 wafer same nitride	USPAT;	2004/02/10
] 30	DOWYS HEATTO WATER SAME HEATTAG	US-PGPUB;	11:05
}			EPO; JPO;	
			DERWENT;	
	0.0	hove2 near10 vator near10 flate4	IBM_TDB USPAT;	2004/02/10
-	96	bow\$3 near10 wafer near10 flat\$4	US-PGPUB;	13:47
	1		EPO; JPO;	
			DERWENT;	
		1	IBM_TDB	2004/02/10
-	687	deposit\$ near15 wafer near10 flat\$4	USPAT; US-PGPUB;	2004/02/10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/02/12
-	70		USPAT; US-PGPUB;	2004/02/10 13:50
		flattening or flattens)	EPO; JPO;	13.30
1			DERWENT;	
			IBM_TDB	
-	3	5562770.URPN.	USPAT	2004/02/10
1_	12		USPAT	13:53
_	12	"3458369" "3808674" "3621033	JULAT	13:54
1		"4415373" "4631804" "4805071"		
		"4830984" "5158907" "5319570").PN.		2004/00/10
-	, 225	direct near5 heat\$4 and 117/\$.ccls.	USPAT; US-PGPUB;	2004/02/10 14:32
			EPO; JPO;	13.52
			DERWENT;	
			IBM_TDB	

-	66	direct near5 heat\$4 and 117/\$.ccls. and	USPAT;	2004/02/10
		(chemical adj vapor adj deposition or	US-PGPUB;	14:36
	1	cvd)	EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	0004/00/10
-	1911	without near4 heat near2 sink	USPAT;	2004/02/10
			US-PGPUB;	14:36
1			EPO; JPO;	
			DERWENT;	
}			IBM_TDB	
-	77		USPAT;	2004/02/10
		or chemical adj vapor adj deposition)	US-PGPUB;	14:38
	İ		EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	2004/02/10
-	6	((without near4 heat near2 sink) and (cvd	USPAT;	2004/02/10
		or chemical adj vapor adj deposition))	US-PGPUB;	14:37
	1	and 117/\$.ccls.	EPO; JPO;	
			DERWENT;]
	_	(-14)	IBM_TDB	2004/02/10
-	5	(without near4 heat near2 sink) same	USPAT;	2004/02/10
		(direct\$4 near2 heat\$4) and (cvd or	US-PGPUB;	14:38
		chemical adj vapor adj deposition)	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	2004/02/23
-	38	ueda near2 tetsuzo.in.	USPAT;	1
			US-PGPUB;	11:18
			EPO; JPO;	
			DERWENT;	i i
		10 2 2	IBM_TDB	2004/02/23
-	0	ammonia near10 partial near2 pressure	USPAT;	
		same (anneal\$ or heat near2 treat\$ or	US-PGPUB;	11:20
		rapid near2 thermal or rta or rtp) same	EPO; JPO;	
		(p\$1type)	DERWENT;	
		" 1 2"10	IBM_TDB	2004/02/23
-	2	1	USPAT;	1 ' '
		or heat near2 treat\$ or rapid near2	US-PGPUB;	11:20
	1	thermal or rta or rtp) same (p\$1type)	EPO; JPO;	
			DERWENT;	
		Who sub 28 noom10 needduro damo /annoale	IBM_TDB USPAT;	2004/02/23
-	3		US-PGPUB;	11:21
		or heat near2 treat\$ or rapid near2		11.21
		thermal or rta or rtp) same resistiv\$	EPO; JPO; DERWENT;	
			IBM TDB	
	1	titanium near2 silicide near10 sputter	USPAT;	2004/09/20
-	1	-	US-PGPUB;	17:02
		near2 temperature	EPO; JPO;	11.02
			DERWENT;	
			IBM TDB	
_	8	(titanium near2 silicide or tisi) same	USPAT;	2004/09/20
_	°	sputter near12 temperature	US-PGPUB;	17:02
		Spaceer Heartz temperature	EPO; JPO;	11.02
İ			DERWENT;	
1			IBM TDB	
1_	1/97	wafer near10 bow\$5	USPAT;	2004/09/27
	140/	Marci Hearto Dowas	US-PGPUB;	16:21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	40	(wafer near10 bow\$5) and (gan or gallium	USPAT;	2004/09/27
	1	(warer hearto bowss) and (gan or garrium near2 nitride)	US-PGPUB;	16:47
	- 3.00	Hours Histage	EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	224	(wafer near10 bow\$5) same flat\$4	USPAT;	2004/09/27
	224	/ "alci Mearle Dowys, Same Ilacyt	US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT;	
	[IBM TDB	
1	I .	I and the second second second second second second second second second second second second second second se	1 7 11 1 1 1 1 1 1	ı

				10004/00/07
-	2580	<pre>(sin or silicon near2 nitride) near10 (deposit\$5 or grow\$4) near10 temperature</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/27 17:00
-	28	(sin or silicon near2 nitride) near10 (deposit\$5 or grow\$4) near10 temperature near10 "650"	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/09/27 17:25
_	119	(gan or gallium near2 nitride) near10	DERWENT; IBM_TDB USPAT;	2004/09/27
		layered near10 substrate	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	17:27
_	84	(gan or gallium near2 nitride) near10 layered near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:36
-	17	(gan or gallium near2 nitride) near10 layered near2 substrate near10 (sapphire or "al.sub.2o.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27
_) 14 •	(gan or gallium near2 nitride) near10 layered adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:38
-	109	epitaxial near5 (gan or gallium adj nitride) near10 (deposit\$5 or grow\$5) near5 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:39
_	25	epitaxial near5 (gan or gallium adj nitride) near10 (deposit\$5 or grow\$5) near5 temperature same MOCVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:44
_	332	thermal near2 expansion near10 (gan or gallium near2 nitride) near2 coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:45
-	94	thermal near2 expansion near2 (gan or gallium near2 nitride) near2 coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:54
_	120	(gan or gallium near2 nitride) same bow\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27
_	18	(gan or gallium near2 nitride) same bow\$5 near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 17:59
	146	tungsten near2 silicide near10 deposit\$5 near5 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28